

Title (en)

WAFER STRUCTURE FOR ELECTRONIC INTEGRATED CIRCUIT MANUFACTURING

Title (de)

WAFERSTRUKTUR ZUR HERSTELLUNG EINER ELEKTRONISCHEN INTEGRIERTEN SCHALTUNG

Title (fr)

STRUCTURE DE TRANCHE POUR LA FABRICATION DE CIRCUITS INTÉGRÉS ÉLECTRONIQUES

Publication

EP 2748848 A4 20150610 (EN)

Application

EP 12826508 A 20120824

Priority

- US 201113218308 A 20110825
- US 201113218273 A 20110825
- US 201113218335 A 20110825
- US 201113218345 A 20110825
- US 201113218352 A 20110825
- US 201113218292 A 20110825
- US 2012052269 W 20120824

Abstract (en)

[origin: WO2013028973A1] A bonded wafer structure having a handle wafer, a device wafer, and an interface region with an abrupt transition between the conductivity profile of the device wafer and the handle wafer is used for making semiconductor devices. The improved doping profile of the bonded wafer structure is well suited for use in the manufacture of integrated circuits. The bonded wafer structure is especially suited for making radiation-hardened integrated circuits.

IPC 8 full level

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CPC (source: EP)

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Citation (search report)

- [X1] WO 9209099 A1 19920529 - BOSCH GMBH ROBERT [DE]
- [X1] US 2009185316 A1 20090723 - SCHNEIDER JENS [DE], et al
- [X1] EP 0889509 A2 19990107 - HARRIS CORP [US]
- [X1] EP 0327316 A2 19890809 - TOSHIBA KK [JP]
- [X1] JP 2008211148 A 20080911 - FUJI ELEC DEVICE TECH CO LTD
- [X] EP 0405422 A1 19910102 - IXYS CORP [US]
- [A] US 2011042576 A1 20110224 - WILSON ROBIN [GB], et al
- [A] US 5466303 A 19951114 - YAMAGUCHI HITOSHI [JP], et al
- [A] DUSSAULT H ET AL: "High energy heavy-ion-induced single event transients in epitaxial structures", IEEE TRANSACTIONS ON NUCLEAR SCIENCE, IEEE SERVICE CENTER, NEW YORK, NY, US, vol. 41, no. 6, 1 December 1994 (1994-12-01), pages 2018 - 2025, XP011386325, ISSN: 0018-9499, DOI: 10.1109/23.340537
- See references of WO 2013028973A1

Designated contracting state (EPC)

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DOCDB simple family (application)

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